XN04608 (XN4608)

Silicon NPN epitaxial planer transistor (Tr1) Silicon PNP epitaxial planer transistor (Tr2)

For general amplification (Tr1) For amplification of low frequency output (Tr2)

Features

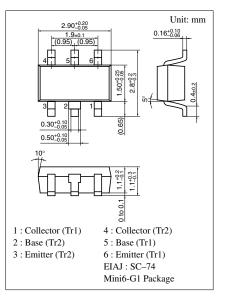
- Two elements incorporated into one package.
- Reduction of the mounting area and assembly cost by one half.

Basic Part Number of Element

• 2SD0601A(2SD601A) + 2SB0970(2SB970)

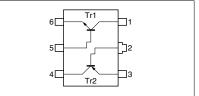
F	Parameter	Symbol	Ratings	Unit	
Tr1	Collector to base voltage	V _{CBO}	60	V	
	Collector to emitter voltage	V _{CEO}	50	V	
	Emitter to base voltage	V _{EBO}	7	V	
	Collector current	I _C	100	mA	
	Peak collector current	I _{CP}	200	mA	
Tr2	Collector to base voltage	V _{CBO}	-15	V	
	Collector to emitter voltage	V _{CEO}	-10	V	
	Emitter to base voltage	V_{EBO}	-7	V	
	Collector current	I _C	- 0.5	А	
	Peak collector current	I _{CP}	-1	А	
Overall	Total power dissipation	P _T	300	mW	
	Junction temperature	Tj	150	°C	
	Storage temperature	T _{stg}	-55 to +150	°C	





Marking Symbol: 5E

Internal Connection



Note) The Part number in the Parenthesis shows conventional part number.

Electrical Characteristics (Ta=25°C)

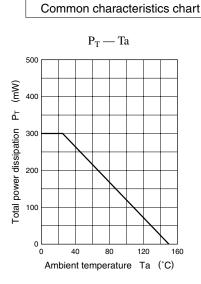
• Tr1

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	60			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = 2mA, I_{\rm B} = 0$	50			v
Emitter to base voltage	V _{EBO}	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	7			v
Collector cutoff current	I _{CBO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
Conector cuton current	I _{CEO}	$V_{CE} = 10V, I_B = 0$			100	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = 10V, I_C = 2mA$	160		460	
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 10 {\rm mA}$		0.1	0.3	v
Transition frequency	f _T	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		3.5		pF

• Tr2

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{\rm C} = -10 \mu A, I_{\rm E} = 0$	-15			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = -1 {\rm mA}, I_{\rm B} = 0$	-10			V
Emitter to base voltage	V _{EBO}	$I_{\rm E} = -10 \mu A, I_{\rm C} = 0$	-7			V
Collector cutoff current	I _{CBO}	$V_{CB} = -10V, I_E = 0$			- 0.1	μA
	h _{FE1}	$V_{CE} = -2V, I_C = -0.5A^*$	100		350	
Forward current transfer ratio	h _{FE2}	$V_{CE} = -2V, I_C = -1A^*$	60			
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -0.4$ A, $I_{\rm B} = -8$ mA		- 0.16	- 0.3	V
Base to emitter saturation voltage	V _{BE(sat)}	$I_{\rm C} = -0.4 {\rm A}, I_{\rm B} = -8 {\rm m} {\rm A}$		- 0.8	-1.2	V
Transition frequency	f _T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		130		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		22		pF

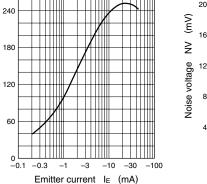
* Pulse measurement

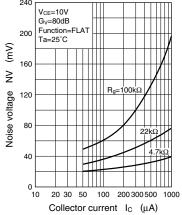


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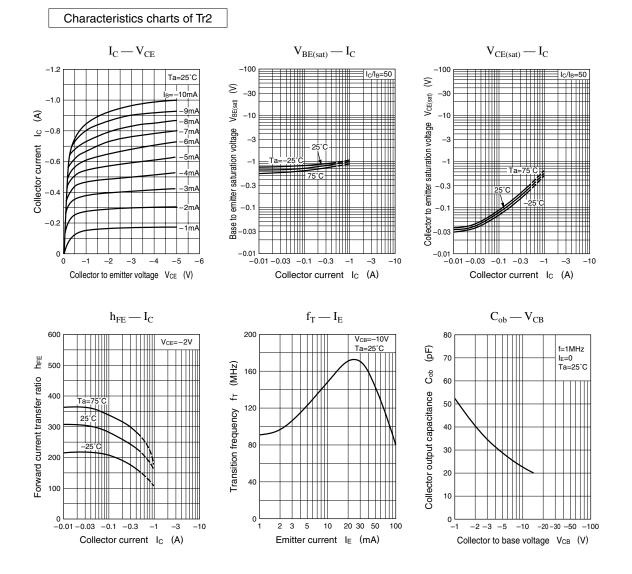
100

Characteristics charts of Tr1 $I_B - V_{BE}$ $I_C - V_{BE}$ $I_C - V_{CE}$ 60 1200 240 Ta=25°C V_{CE}=10V V_{CE}=10V I_B=160μA Ta=25°C 1000 200 50 Collector current Ic (mA) Collector current Ic (mA) 14ģμA (hl) ⁸⁰⁰ 40 160 120¦µA <u>__</u> 100µA Base current 25° C 30 120 600 ł 80µA Ta=75 25 80 20 60µ A 400 40μ A 10 200 40 20µA 0 -0 0 2 4 6 10 0.2 0.4 0.6 0.8 1.0 0 0.4 0.8 1.2 1.6 0 8 Base to emitter voltage V_{BE} (V) Collector to emitter voltage VCE (V) Base to emitter voltage VBE (V) $I_C - I_B$ V_{CE(sat)} — I_C $h_{FE} - I_C$ 240 100 600 $I_C/I_B=10$ V_{CE}=10V V_{CE}=10V Ta=25°C S 30 hFE Collector to emitter saturation voltage VCE(sat) 500 200 Collector current Ic (mA) Forward current transfer ratio 10 160 400 3 120 300 1 0.3 200 80 25 0.1 100 40 0.03 0.01 L 0.1 4 م 0 L 0 200 400 600 800 1000 0.3 3 10 30 100 0.3 3 10 30 1 1 Base current IB Collector current Ic (mA) Collector current Ic (mA) (µA) $f_T - I_E$ $NV - I_C$ 300 240 V_{CB}=10V V_{CE}=10V G_V=80dB Ta=25°C Function=FLAT Ta=25°C 200 Transition frequency fr (MHz) 240 160





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